

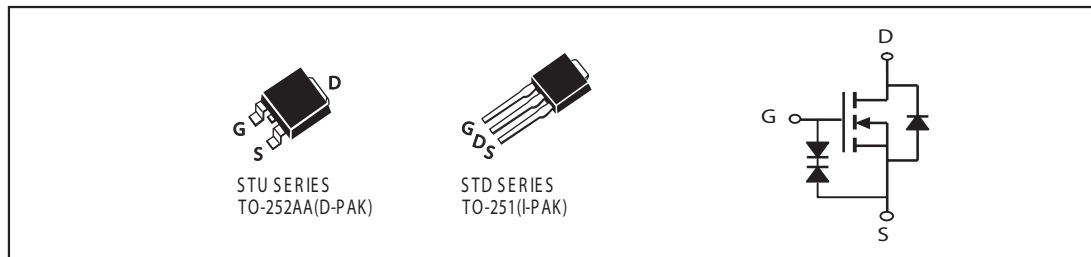


N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(ON)} (mΩ) Max
40V	30A	20 @ V _{GS} = 10V
		30 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ^a @ T _c =25°C -Pulsed ^b	I _D	30	A
	I _{DM}	100	A
Drain-Source Diode Forward Current	I _S	8	A
Maximum Power Dissipation @ T _c =25°C	P _D	50	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

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ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 32V, V _{GS} = 0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±10	uA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250uA	1	1.9	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 10A		16	20	m ohm
		V _{GS} = 4.5V, I _D = 8A		23	30	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	30			A
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 10A		17		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz		690		pF
Output Capacitance	C _{OSS}			140		pF
Reverse Transfer Capacitance	C _{RSS}			95		pF
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 15V I _D = 1 A V _{GS} = 10V R _{GEN} = 3 ohm		13.1		ns
Rise Time	t _r			13.5		ns
Turn-Off Delay Time	t _{D(OFF)}			45.7		ns
Fall Time	t _f			11.8		ns
Total Gate Charge	Q _g	V _{DS} = 20V, I _D = 10A, V _{GS} = 10V		13.5		nC
		V _{DS} = 20V, I _D = 10A, V _{GS} = 4.5V		6.7		nC
Gate-Source Charge	Q _{gs}	V _{DS} = 20V, I _D = 10A		1.65		nC
Gate-Drain Charge	Q _{gd}	V _{GS} = 10V		3.85		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 8A$		0.84	1.3	V

Notes

- a. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

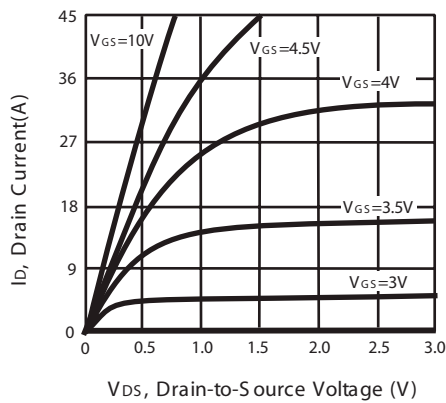


Figure 1. Output Characteristics

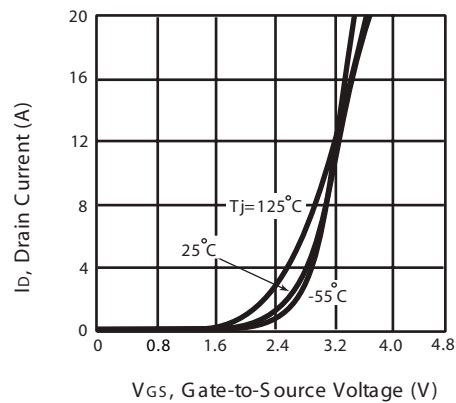


Figure 2. Transfer Characteristics

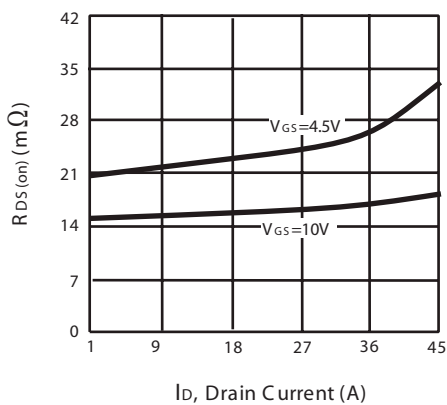


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

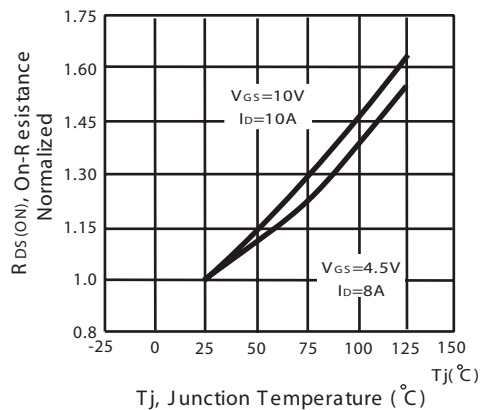


Figure 4. On-Resistance Variation with Drain Current and Temperature

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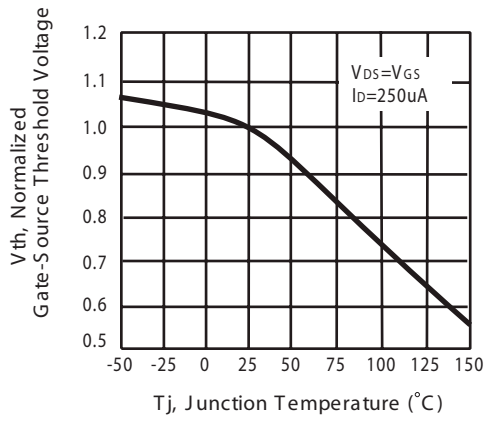


Figure 5. Gate Threshold Variation with Temperature

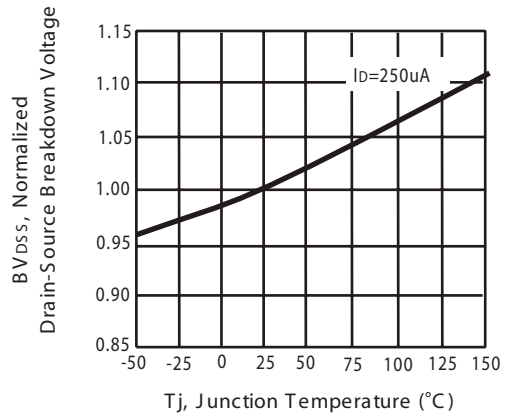


Figure 6. Breakdown Voltage Variation with Temperature

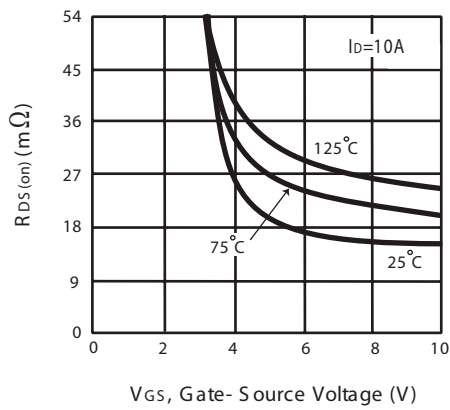


Figure 7. On-Resistance vs. Gate-Source Voltage

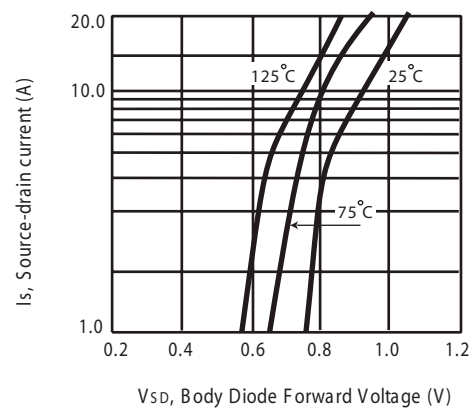


Figure 8. Body Diode Forward Voltage Variation with Source Current

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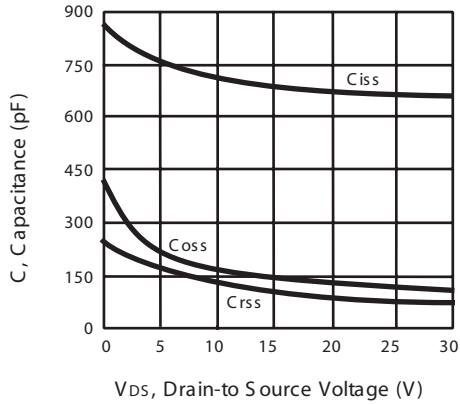


Figure 9. Capacitance

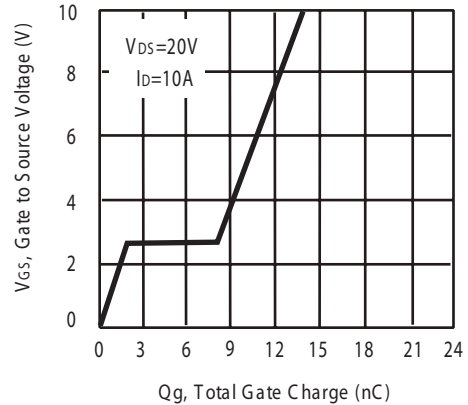


Figure 10. Gate Charge

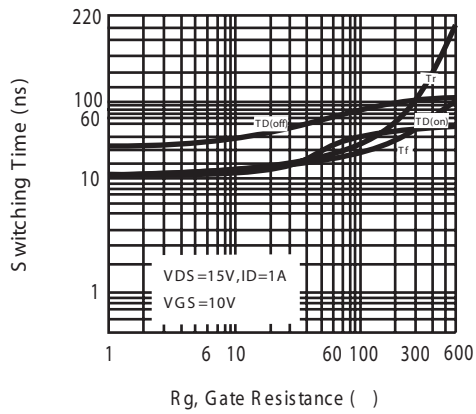


Figure 11. switching characteristics

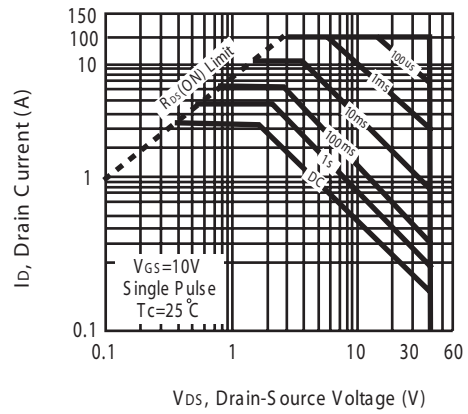


Figure 12. Maximum Safe Operating Area

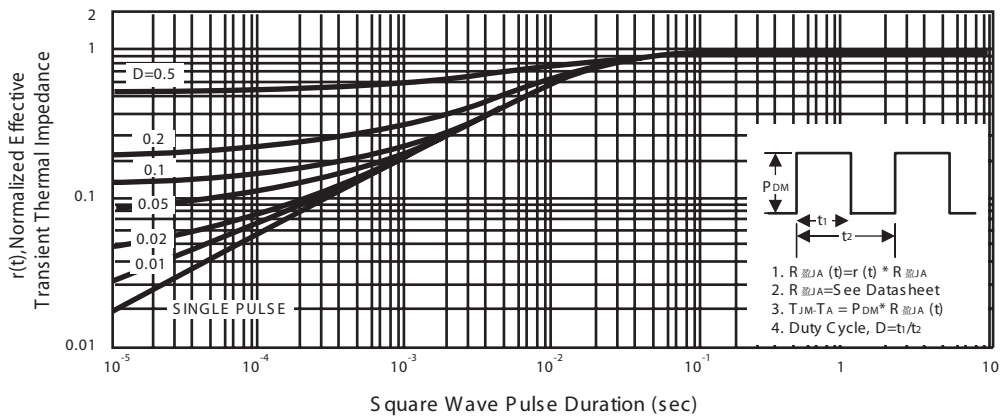
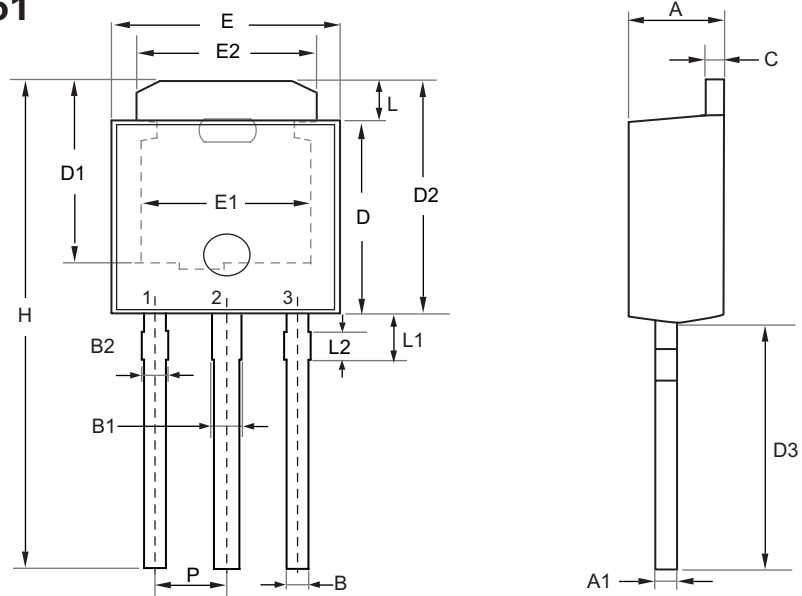


Figure 13. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

TO-251

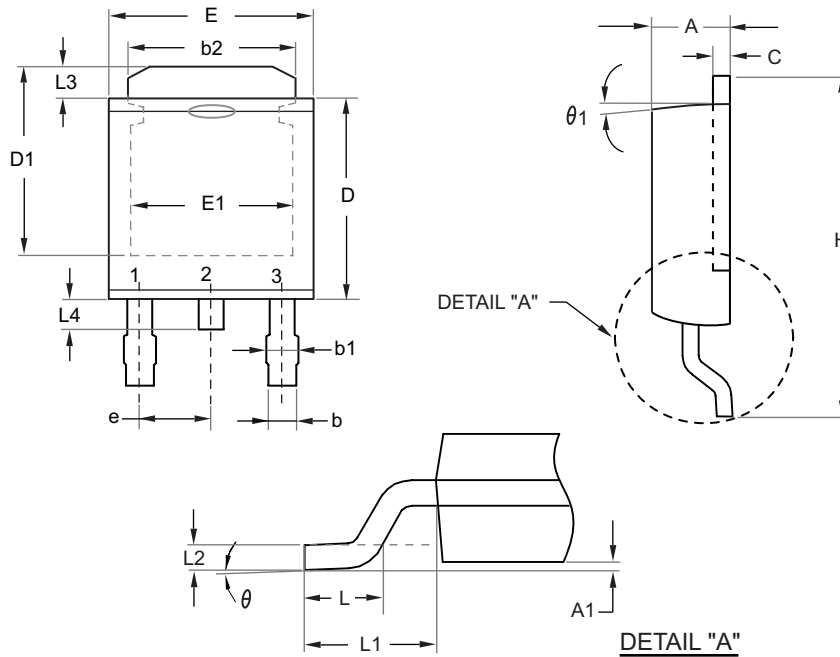


SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

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PACKAGE OUTLINE DIMENSIONS

TO-252

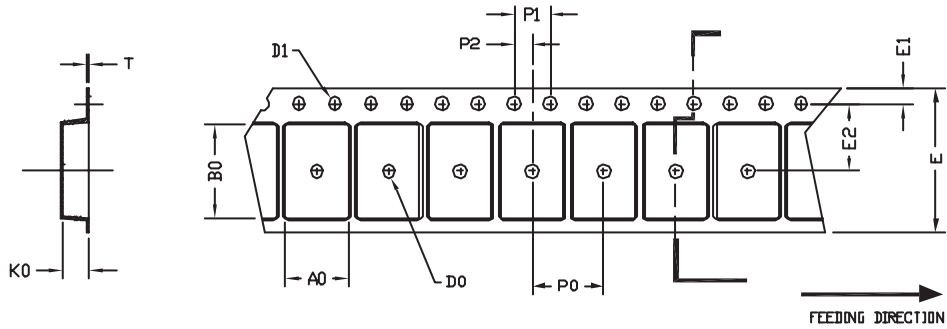


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ_1	7° REF.		7° REF.	

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TO-252 Tape and Reel Data

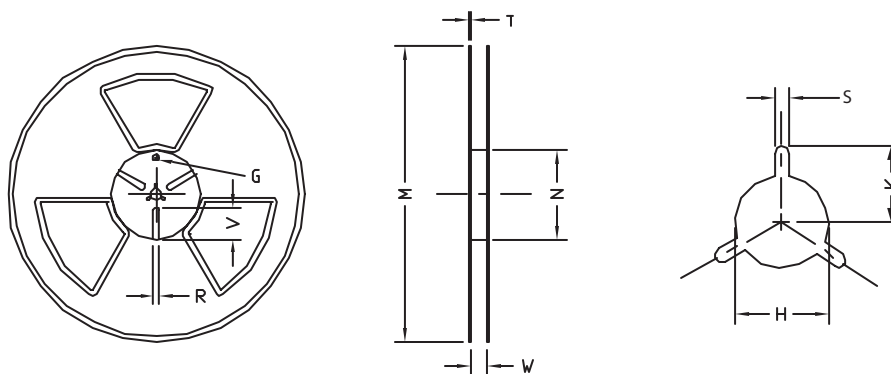
TO-252 Carrier Tape



UNIT: ɓ

PACKAGE	A0	B0	K0	D0	D1	E	E 1	E 2	P0	P1	P2	T
TO-252 (16 ɓ I)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	榎2	榎1.5 +0.1 -0	16.0 0.3 * ɓ	1.75 0.1 * ɓ	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT: ɓ

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ɓ	榎 330	榎330 ±0.5	榎97 ±1.0	17.0 +1.5 -0	2.2	榎13.0 +0.5 -0.2	10.6	2.0 ±0.5	---	---	---